

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the above-referenced application.

Listing of Claims:

Claims 1 – 19 (Cancelled)

¹ ~~20.~~ (Currently amended) A semiconductor device, comprising:

a semiconductor substrate;

an organic film having low dielectric constant and including no silicon, said organic film being formed on said semiconductor substrate; and

at least two silicon included organic films formed on lower and upper surfaces of said organic film having low dielectric constant, wherein a first silicon included organic film is formed on said lower surface facing said semiconductor substrate and a second silicon included organic film is formed on said upper surface, and wherein said second silicon included organic film is larger in thickness than said first silicon included organic film.

² ~~21.~~ (Previously presented) A semiconductor device as claimed in claim ¹~~20~~, wherein a conductive film is selectively buried into an opening portion of stacked films consisting of said silicon included organic films formed on said lower and upper surfaces of said organic film having low dielectric constant.

3 22. (Original) A semiconductor device as claimed in claim 20¹, wherein said silicon included organic film is formed by a polymer of divinyl-siloxane-benzocyclobutene.

5 23. (Currently amended) A semiconductor device, comprising:
at least two silicon included organic films composed of a first organic compound including silicon; and
a silicon non-included organic film which is composed of a second organic compound including substantially no silicon and which is disposed between said silicon included organic films, wherein said silicon non-included organic film has an upper surface and a lower surface facing a substrate, and wherein said silicon included organic film disposed on said upper surface is larger in thickness than said silicon included organic film disposed on said lower surface.

10 24. (Currently amended) A semiconductor device, comprising:

a substrate;

a first silicon included organic film which is formed on an upper side of said substrate and which is composed of a first organic compound including silicon;

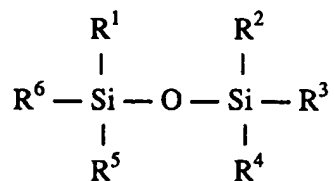
a silicon non-included organic film which is formed on an upper side of said first silicon included organic film and which is composed of a second organic compound including substantially no silicon ~~and in which a wiring trench is formed down to said first silicon included organic film;~~

a second silicon included organic film which is formed on an upper side of said silicon non-included organic film; [[and]]

a lower wiring trench formed through said second silicon included organic film, said silicon non-included organic film and down to and through said first silicon included organic film; and

a conductor formed within said lower wiring trench.

6 25. (Previously presented) A semiconductor device as claimed in claim 23, wherein said first organic compound includes a polymer of a compound having the following structural formula;



wherein R¹ through R⁶ are hydrocarbon radicals.

7 26. (Original) A semiconductor device as claimed in claim 23^S, wherein said first organic compound includes a polymer of divinyl-siloxane-benzocyclobutene.

8 27. (Original) A semiconductor device as claimed in claim 23^S, wherein said first organic compound includes a polymer of siloxane-polyimide.

14 28. (Currently amended) A semiconductor device, comprising:

an organic film composed of an organic compound including no silicon;

a hard mask, wherein said hard mask is for use in etching ~~[[an]]~~ said organic film composed of ~~[[an]]~~ the organic compound including no silicon, said hard mask including a first organic compound including silicon; and

an etching stopper film, wherein said etching stopper film is for use in etching said organic film composed of the organic compound including no silicon, said etching stopper film including a second organic compound including silicon;

wherein said hard mask is disposed on an upper surface of said organic film composed of an organic compound including no silicon and said etching stopper film is disposed on a lower surface of said organic film, and wherein said hard mask is larger in thickness than said etching stopper film.

29. (Cancelled)

4 30. (New) The semiconductor device of claim 20¹, further comprising:

a wiring trench formed through said second silicon included organic film, said silicon non-included organic film and down to and through said first silicon included organic film.

9 31. (New) The semiconductor device of claim 23⁴, further comprising:

a wiring trench formed through said second silicon included organic film, said silicon non-included organic film and down to and through said first silicon included organic film.

15 32. (New) The semiconductor device of claim 28¹⁴, further comprising:

a wiring trench formed through said hard mask, said organic film and down to and through said etching stopper film.

33. (New) The semiconductor device of claim 24¹⁰, wherein said second silicon organic film is larger in thickness than said first silicon organic film.

11 34. (New) The semiconductor device of claim 24¹⁰, further comprising:

at least one additional wiring trench disposed on said first silicon second silicon included organic film, said silicon non-included organic film and said first silicon included organic film.

1 2 35. (New) The semiconductor device of claim 24, further comprising:

an upper wiring structure disposed over said first silicon included organic film,
wherein said upper wiring structure includes a first upper silicon included organic film,
an upper silicon non-included organic film, a second upper silicon included organic film
and at least one upper wiring trench disposed therein.

1 3 36: (New) The semiconductor device of claim 35, wherein said at least one upper wiring trench
includes a first upper trench extending through said upper wiring structure in contact with
said lower wiring trench and a second upper trench extending through said first upper
silicon included organic film and said upper silicon non-included organic film.